

2N4272

BIPOLAR NPN

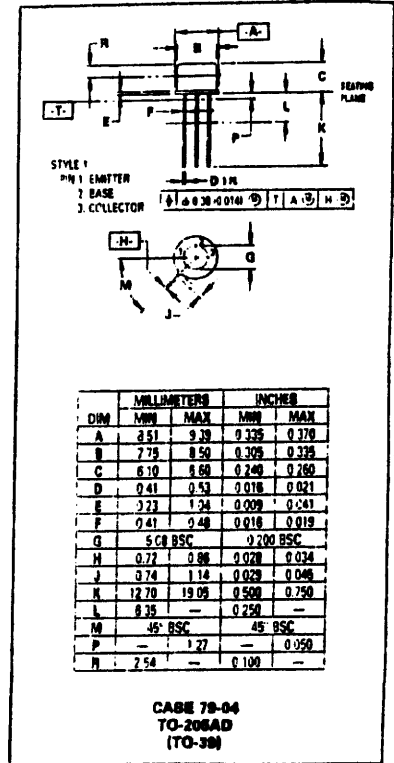
SILICON TRANSISTOR

FEATURES

- GENERAL PURPOSE NPN TRANSISTOR
- HERMETICALLY SEALED METAL PACKAGE

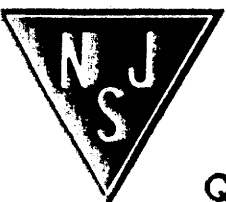
ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{CBO}	Collector – Base Voltage	180V
V_{CEO}	Collector – Emitter Voltage	140V
V_{EBO}	Emitter – Base Voltage	6V
I_C	Continuous Collector Current	2.5A
P_{tot}	Power Dissipation	10W
$R_{\theta JC}$	Thermal Resistance Junction to Case	15°C/W
T_J, T_{stg}	Operating and Storage Temperature	-55 to 175°C



ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CBO}$	Collector – Base Breakdown Voltage $I_C = 100\mu A$ $I_E = 0$	180			V
$V_{(BR)CEO}$	Collector – Emitter Breakdown Voltage $I_C = 10mA$ $I_B = 0$	140			
$V_{(BR)EBO}$	Emitter – Base Breakdown Voltage $I_E = 100\mu A$ $I_C = 0$	6			
I_{CBO}	Collector – Base Cut-off Current $V_{CB} = 175V$ $I_E = 0$			100	μA
I_{CEO}	Collector – Emitter Cut-off Current $V_{CE} = 10V$ $I_B = 0$			10	mA
$V_{CE(sat)}$	Collector – Emitter Saturation Voltage $I_C = 500mA$ $I_B = 50mA$			0.6	V
V_{BE}	Base – Emitter Voltage $I_C = 1A$ $V_{CE} = 10V$			1.1	
h_{FE}	Static Forward Current Transfer Ratio $I_C = 1A$ $V_{CE} = 10V$	20		140	—



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

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